

DMN53D0LW-7 Datasheet



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DiGi Electronics Part Number	DMN53D0LW-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN53D0LW-7
Description	MOSFET N-CH 50V 360MA SOT323
Detailed Description	N-Channel 50 V 360mA (Ta) 320mW (Ta) Surface Mount SOT-323



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

DMN53D0LW-7

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

50 V

Drive Voltage (Max Rds On, Min Rds On):

5V, 10V

Vgs(th) (Max) @ Id:

1.5V @ 100 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-323

Base Product Number:

DMN53

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

360mA (Ta)

Rds On (Max) @ Id, Vgs:

20hm @ 270mA, 10V

Gate Charge (Qg) (Max) @ Vgs:

1.2 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

45.8 pF @ 25 V

Power Dissipation (Max):

320mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

SC-70, SOT-323

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN53D0LW

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	2.0Ω @ V _{GS} = 10V	360mA
	3.0Ω @ V _{GS} = 5V	250mA

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

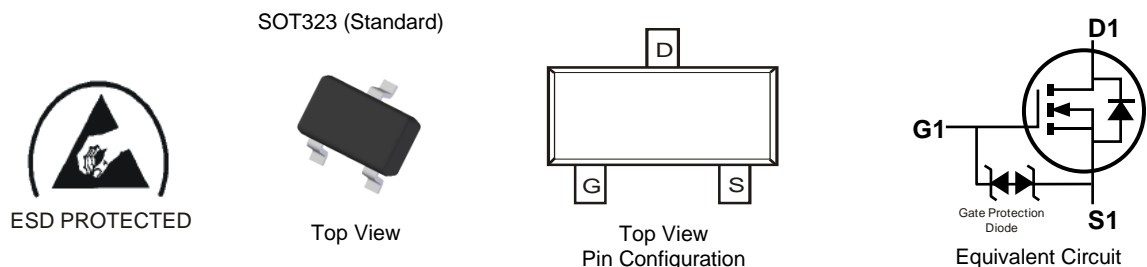
- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 **(e3)**
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

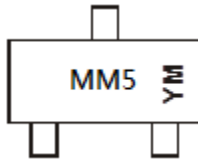


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN53D0LW-7	SOT323 (Standard)	3,000	Tape & Reel
DMN53D0LW-13	SOT323 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MM5 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: L = 2024)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2013	...	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	A	...	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	I_D	Steady State	mA
		$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	
Continuous Drain Current (Note 6) $V_{GS} = 5\text{V}$	I_D	Steady State	mA
		$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	700	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation	P_D	(Note 5)	320
		(Note 6)	420
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5)	395
		(Note 6)	301
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.



DMN53D0LW

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	—	1.5	V	V _{DS} = V _{GS} , I _D = 100μA
Gate Threshold Voltage Temperature Coefficient (Note 8)	$\frac{\Delta V_{GS(TH)}}{\Delta T_J}$	—	-3.4	—	mV/°C	—
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.73	2.0	Ω	V _{GS} = 10V, I _D = 270mA
		—	0.77	3.0		V _{GS} = 5V, I _D = 200mA
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 200mA
Diode Forward Voltage	V _{SD}	—	0.75	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	45.8	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	5.3	—		
Reverse Transfer Capacitance	C _{rss}	—	3.9	—		
Total Gate Charge V _{GS} = 10V	Q _g	—	1.2	—	nC	V _{GS} = 10V, V _{DS} = 10V, I _D = 250mA
Total Gate Charge V _{GS} = 4.5V	Q _g	—	0.6	—		
Gate-Source Charge	Q _{gs}	—	0.2	—		
Gate-Drain Charge	Q _{gd}	—	0.1	—		
Turn-On Delay Time	t _{D(ON)}	—	2.7	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _R	—	2.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	18.9	—		
Turn-Off Fall Time	t _F	—	11.0	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.



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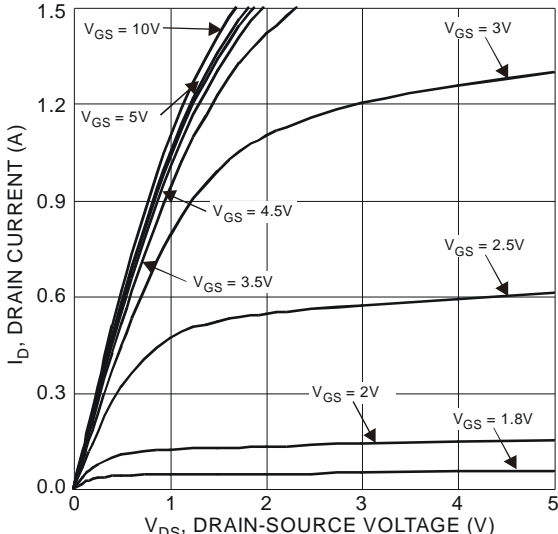


Figure 1 Typical Output Characteristics

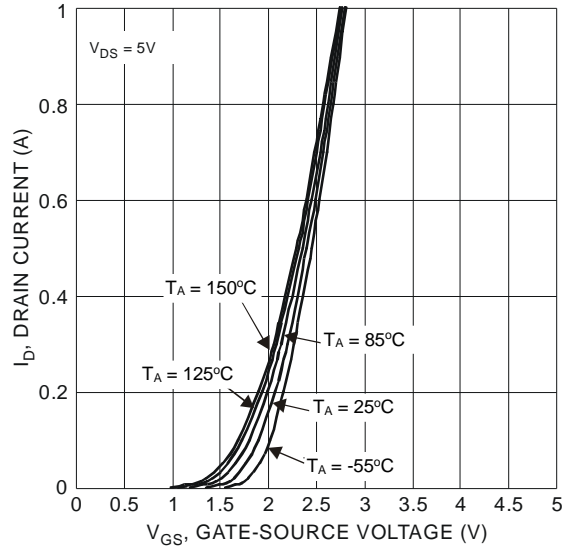


Figure 2 Typical Transfer Characteristics

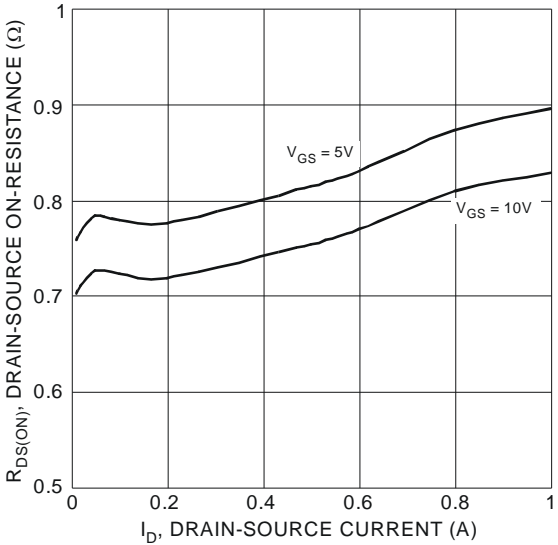


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

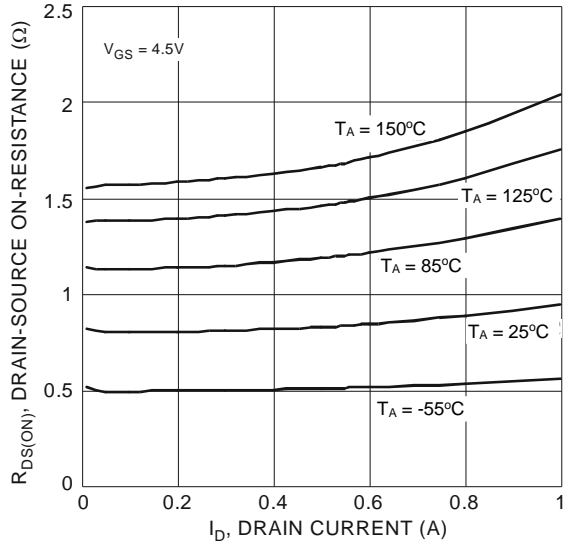


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

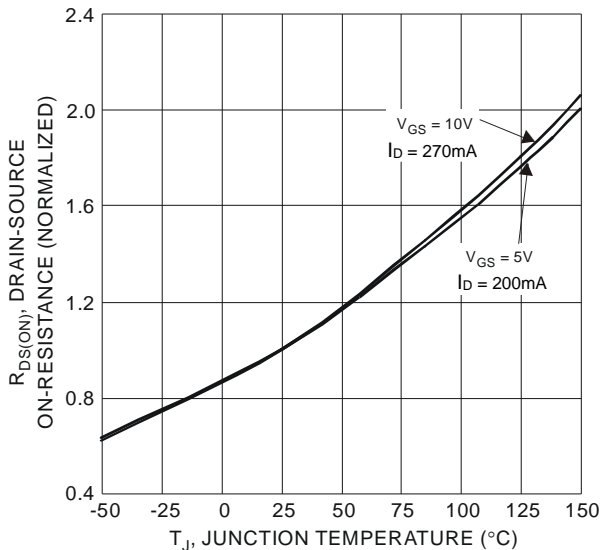


Figure 5 On-Resistance Variation with Temperature

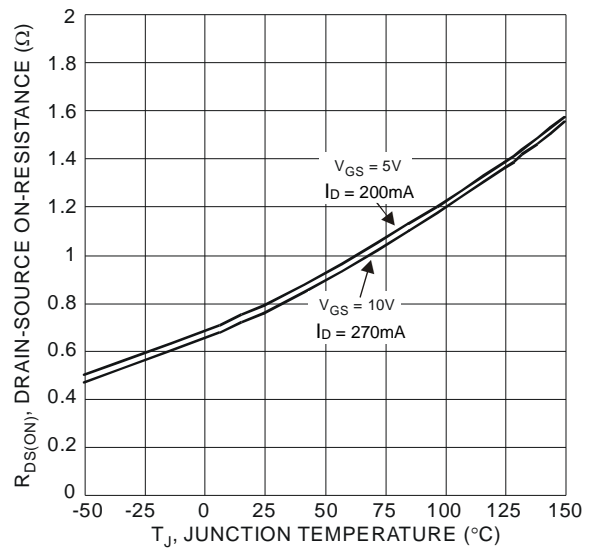


Figure 6 On-Resistance Variation with Temperature



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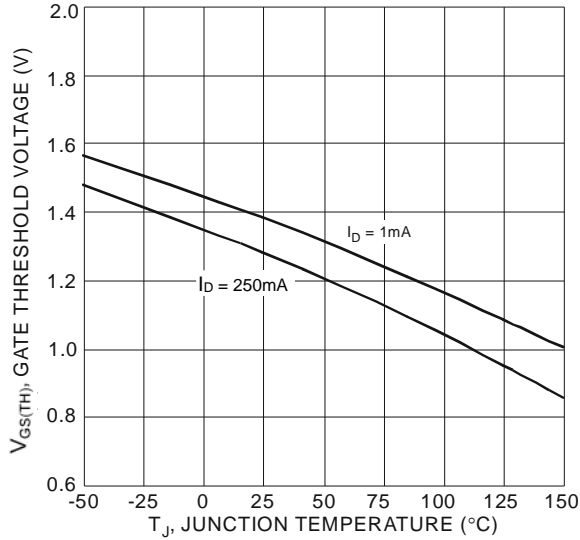


Figure 7 Gate Threshold Variation vs. Junction Temperature

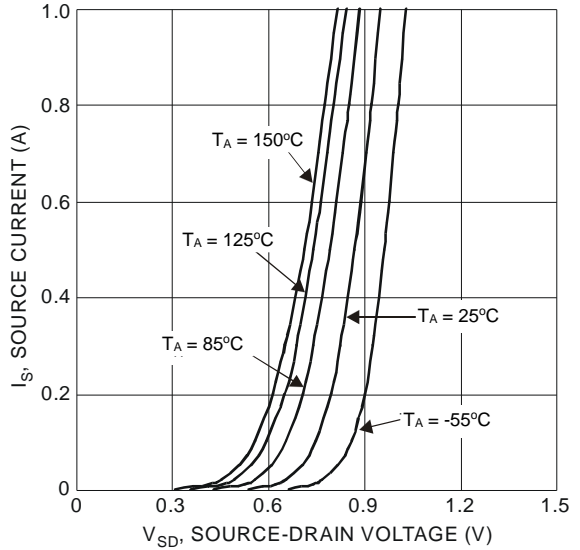


Figure 8 Diode Forward Voltage vs. Current

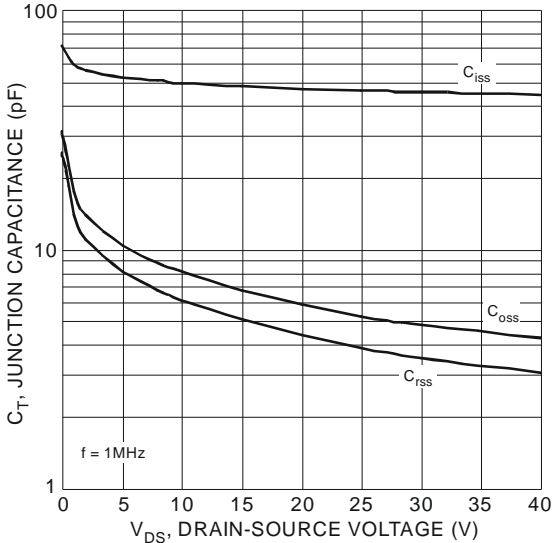


Figure 9 Typical Junction Capacitance

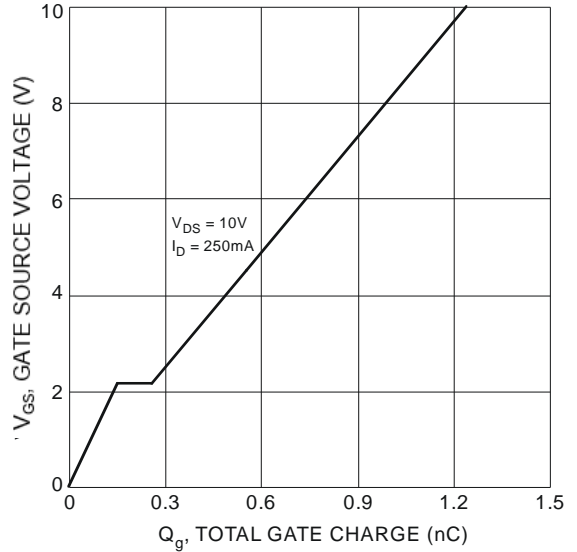


Figure 10 Gate Charge

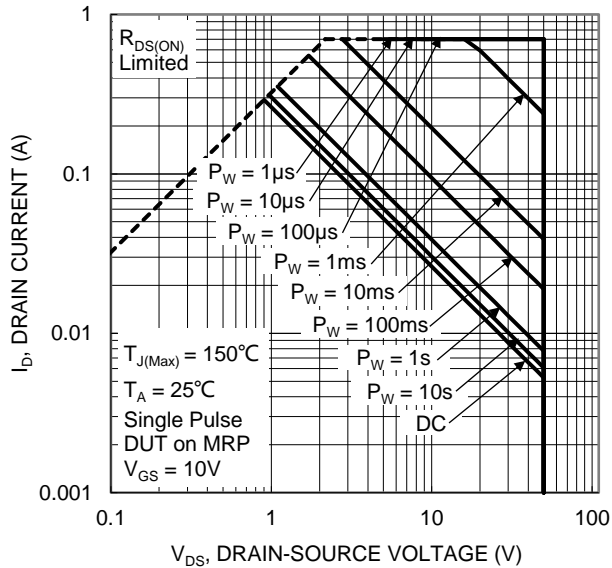
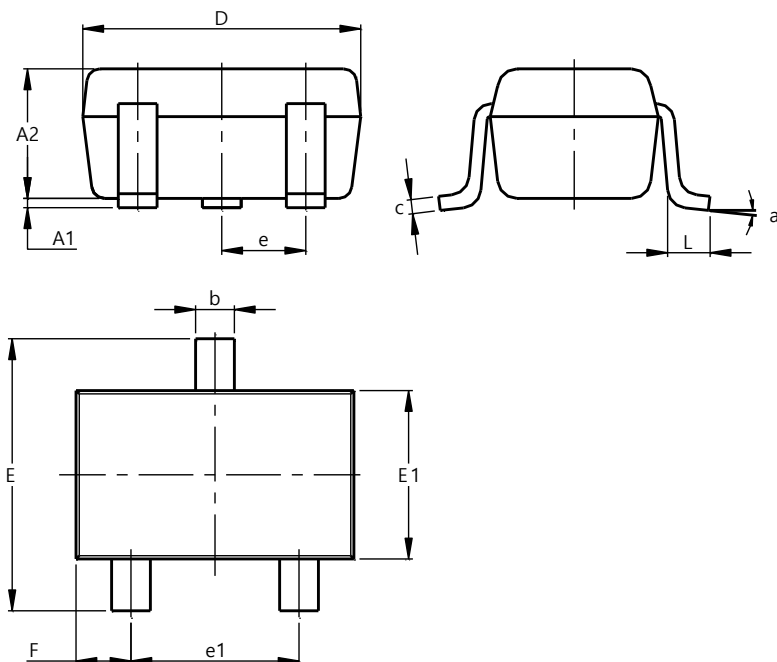


Figure 11 SOA, Safe Operation Area

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323 (Standard)

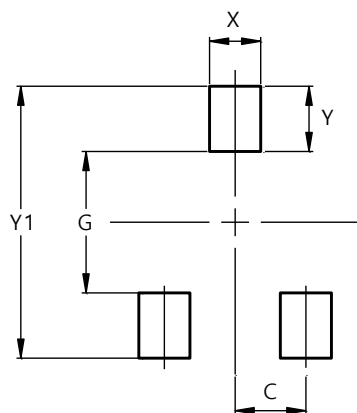


SOT323 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.20	0.40	0.30
c	0.08	0.18	0.13
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
e1	1.20	1.40	1.30
F	0.25	0.475	0.3625
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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